

## 3 A High Voltage Schottky Barrier Rectifier

#### DESCRIPTION

This UPS3100e3 in the Powermite3<sup>®</sup> package is a high efficiency Schottky rectifier that is also RoHS compliant offering high current/power capabilities previously found only in much larger packages. They are ideal for SMD applications that operate at high frequencies. In addition to its size advantages, the Powermite3<sup>®</sup> package includes a full metallic bottom that eliminates the possibility of solder flux entrapment during assembly and a unique locking tab act as an efficient heat path to the heat-sink mounting. Its innovative design makes this device ideal for use with automatic insertion equipment.

IMPORTANT: For the most current data, consult MICROSEMI's website: http://www.microsemi.com

#### **ABSOLUTE MAXIMUM RATINGS AT 25° C** (UNLESS OTHERWISE SPECIFIED) Symbol Unit Rating Value Peak Repetitive Reverse Voltage V<sub>RRM</sub> Working Peak Reverse Voltage 100 V VRWM DC Blocking Voltage $V_R$ **RMS Reverse Voltage** 70 V V<sub>R(RMS)</sub> Average Rectified Output Current 3 $I_0$ А Non-Repetitive Peak Forward Surge Current 8.3ms Single half sine wave Superimposed 50 А I<sub>FSM</sub> on Rated Load@ T<sub>c</sub> =90 °C

### THERMAL CHARACTERISTICS

T<sub>STG</sub>

 $T_{\rm J}$ 

-55 to +150

-55 to +125

°C

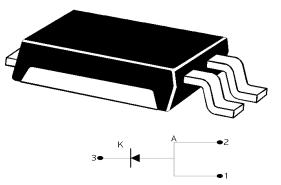
°С

Thermal Resistance				
Junction-to-Case (bottom)	R <sub>θJC</sub>	2.5	°C/ Watt	
Junction to Ambient (1)	R <sub>0JA</sub>	65	°C/ Watt	
(1) When mounted on FR-4 PC board using 2 oz copper with recommended minimum foot print				

#### Powermite 3<sup>™</sup>

Storage Temperature

Junction Temperature



### **KEY FEATURES**

- Very low thermal resistance package
- RoHS Compliant with e3 suffix part number
- Guard-ring-die construction for transient protection
- Efficient heat path with Integral locking bottom metal tab
- Low forward voltage
- Full metallic bottom eliminates flux entrapment
  - Compatible with automatic insertion
- Low profile-maximum height of 1mm

#### **APPLICATIONS/BENEFITS**

- Switching and Regulating Power Supplies.
  Silicon Schottky (bot corrier) rectifier for
- Silicon Schottky (hot carrier) rectifier for minimal reverse voltage recovery
- Elimination of reverse-recovery oscillations to reduce need for EMI filtering
- Charge Pump Circuits
- Reduces reverse recovery loss with low  ${\rm I}_{\rm RM}$
- Small foot print 190 X 260 mils (1:1 Actual size) See mounting pad details on pg 3

#### **MECHANICAL & PACKAGING**

- CASE: Void-free transfer molded thermosetting epoxy compound meeting UL94V-0
- FINISH: Annealed matte-Tin plating over copper and readily solderable per MIL-STD-750 method 2026 (consult factory for Tin-Lead plating)
- POLARITY: See figure (left)
- MARKING: S3100•
- WEIGHT: 0.072 gram (approx.)
- Package dimension on last page
- Tape & Reel option: 16 mm tape per Standard EIA-481-B, 5000 on 13" reel

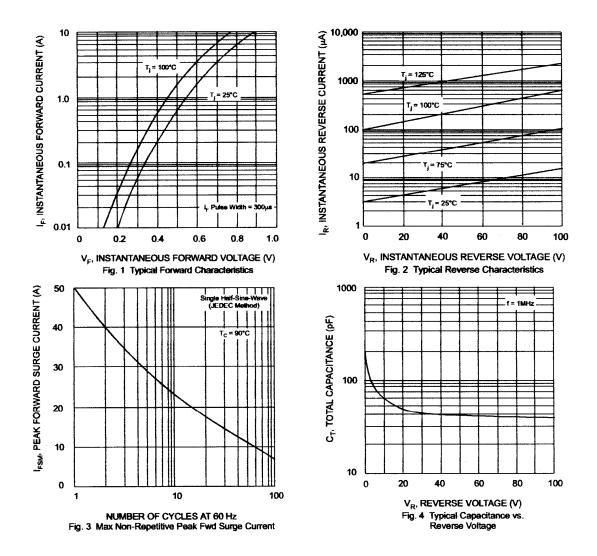
**UPS3100E**3



## 3 A High Voltage Schottky Barrier Rectifier

Parameter	Symbol	Conditions	Min	Тур.	Max	Units
Forward Voltage (Note 1)	V <sub>F</sub>	I <sub>F</sub> = 3 A , T <sub>j</sub> =25 °C I <sub>F</sub> = 3 A , T <sub>j</sub> =100 °C I <sub>F</sub> = 6 A , T <sub>j</sub> =25 °C I <sub>F</sub> = 6 A , T <sub>j</sub> =100 °C		0.72 0.60 0.79 0.68	0.76 0.64 0.83 0.72	V
Reverse Break Down Voltage (Note 1)	V <sub>BR</sub>	I <sub>R</sub> = 0.2 mA	100			V
Reverse Current (Note1)	I <sub>F</sub>	V <sub>R</sub> = 100V, T <sub>j</sub> = 25 °C V <sub>R</sub> = 100V, T <sub>j</sub> =100 °C		1.5 0.5	200 20	μA mA
Capacitance	CT	V <sub>R</sub> = 4 V; f = 1 MHz		85		pF

Note: 1 Short duration test pulse used to minimize self - heating effect.

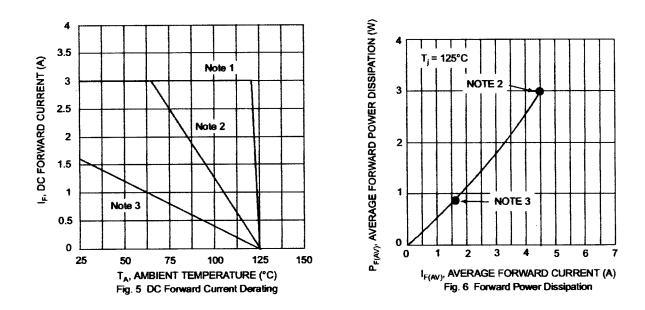


Microsemi

UPS3100E3 ELECTRICALS



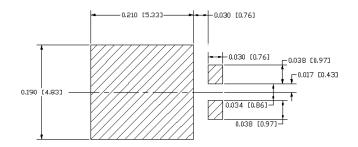
### 3 A High Voltage Schottky Barrier Rectifier



Notes: 1.  $T_A = T_{SOLDERING POINT}$ ,  $R_{\Theta JS} = 2.5$ C/W,  $R_{\Theta SA} = 0^{\circ}$ C/W.

- 2. Device mounted on GETEK substrate, 2" x 2", 2 oz. copper , double-sided , cathode pad dimensions 0.75" x 1.0", anode pad dimensions 0.25" x 1.0".  $R_{\Theta JA}$  in range of 20-35°C/W.
- 3. Device mounted on FRA-4 substrate, 2" x 2", 2 oz. copper, single-sided, pad layout  $R_{\Theta JA}$  in range of 65°C/W. See mounting pad below.

### MOUNTING PAD DIMENSIONS



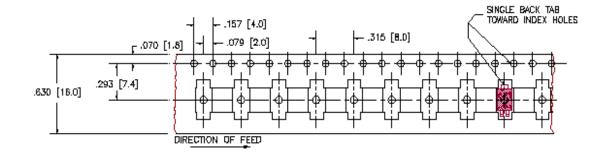
Mounting Pad Dimensions: inches [mm]

**UPS3100E3** 

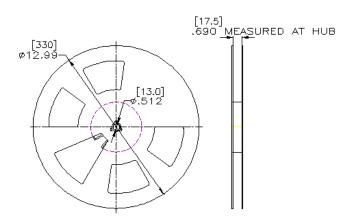


3 A High Voltage Schottky Barrier Rectifier

### TAPE & REEL



13 INCH REEL



MECHANICAL

**UPS3100E3** 



3 A High Voltage Schottky Barrier Rectifier

**POWERMITE®3** 

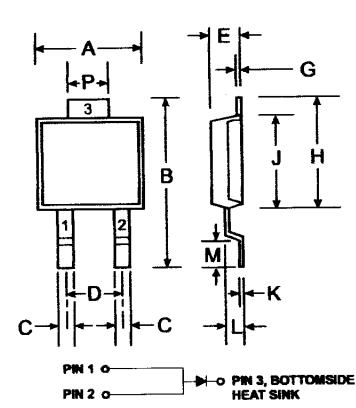
Min

Di-

İ

May

#### PACKAGE DIMENSIONS



		MAA		
A	4.03	4.09		
B	6.40	6.61		
С	.889 NOM			
D	1.83 NOM			
E	1.10	1.14		
G	.178 NOM			
Н	5.01	5.17		
J	4.37	4.43		
K	.178 NOM			
L	.71	.77		
M	.36	.46		
Р	1.73	1.83		
All Dimensions in mm				

Note: Pins 1 & 2 must be electrically connected at the printed circuit board.

# **Mouser Electronics**

Authorized Distributor

Click to View Pricing, Inventory, Delivery & Lifecycle Information:

Microchip: UPS3100E3/TR13 UPS3100/TR13